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WHAT IS CLAIMED IS:

- 1. A variable capacitor structure, comprising:
 - a substrate;
- a first type ion-doped well within the substrate, wherein the first type iondoped well has a cavity:
 - a first-type ion-doped buried layer in the substrate underneath the first type ion-doped well, wherein the first type ion-doped buried layer and the first type ion-doped well are connected;
 - a second type ion-doped region at the bottom of the cavity of the first type ion-doped well; and
 - a conductive layer over the first type ion-doped buried layer, wherein the conductive layer and the first type ion-doped buried layer are connected.
 - The variable capacitor of claim 1, wherein the structure further includes a first metal silicide layer over the second type ion-doped region.
 - The variable capacitor of claim 1, wherein the conductive layer further includes a second type ion-doped deep collector region.
 - 4. The variable capacitor of claim 3, wherein the structure further includes a second metal silicide layer over the second type ion-doped deep collector region.
 - 5. The variable capacitor of claim 1, wherein the conductive layer includes a contact.
 - 6. The variable capacitor of claim 5, wherein the second type ion-doped region and the conductive layer are located within the same active device region of the substrate, and the conductive layer is isolated from the second type ion-doped region through an insulation layer.

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- 7. The variable capacitor of claim 1, wherein the structure further includes a second metal silicide layer between the first type ion-doped buried layer and the conductive layer.
- 8. The variable capacitor of claim 1, wherein the structure further includes an isolation structure within the first type ion-doped well between the second type ion-doped region and the conductive layer.
- 9. The variable capacitor of claim 1, wherein the first type ion-doped buried layer is an N-type buried layer and the second type ion-doped region is a P-doped region.
 - 10. A variable capacitor structure, comprising:
 - a substrate;
- a first type ion-doped well within the substrate, wherein the first type ion-doped region has a shallow trench isolation structure;
- a first type ion-doped buried layer in the substrate underneath the first type ion-doped well, wherein the first type ion-doped buried layer and the first type ion-doped well are connected;
- 15 at least one second type ion-doped region in the first type ion-doped well at the bottom of the shallow trench isolation structure; and
 - at least one first conductive layer connected to the first type ion-doped buried layer.
 - 11. The variable capacitor of claim 10, wherein the first type ion-doped buried layer is an N-type buried layer and the second type ion-doped region is a P-doped region.
 - 12. The variable capacitor of claim 10, wherein the structure further includes at least a second conductive laver connected with the second type ion-doped region.

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- 13. The variable capacitor of claim 10, wherein the structure further includes a metal silicide layer between the first type ion-doped buried layer and the first conductive layer.
 - 14. A method of forming a variable capacitor, comprising the steps of:

providing a substrate having a first type ion-doped buried layer and a first type

5 ion-doped well, wherein the first type ion-doped buried layer is above and in connection to
the first type ion-doped well;

forming a conductive layer in the substrate above the first type ion-doped buried layer;

removing a portion of the first type ion-doped well to form at least one first opening without exposing the first type ion-doped buried layer; and

forming a second type ion-doped region in the first type ion-doped well at the bottom of the first opening.

15. The method of claim 14, wherein the conductive layer is formed before the first opening, including:

forming a second type ion-doped deep collector region in the substrate above the first type ion-doped buried layer such that the second type ion-doped deep collector region and the first type ion-doped buried layer are connected.

16. The method of claim 14, wherein the conductive layer is formed after the second type ion-doped region, including:

removing a portion of the second type ion-doped region and a portion of the first type ion-doped well between the second type ion-doped region and the first type ion-doped buried layer to form a second opening that exposes a portion of the first type ion-doped buried layer; and

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depositing conductive material into the second opening.

- 17. The method of claim 16, wherein the second opening and the first opening are formed in different active device regions of the substrate.
- 18. The method of claim 16, wherein the second opening and the first opening are formed in the same active device region of the substrate.
 - 19. The method of claim 16, wherein after the step of forming the second opening, further includes forming a second isolation spacer.
 - 20. The method of claim 14, wherein after the step of forming the second type ion-doped region, further includes forming a metal silicide layer on the second type ion-doped region and the conductive layer.
 - 21. The method of claim 14, wherein between the step of forming the opening and the second type ion-doped region, further includes forming a first isolation spacer on the sidewalls of the first opening.
 - 22. A method of forming a variable capacitor, comprising the steps of:

providing a substrate having a first type ion-doped buried layer and a first type ion-doped well, wherein the first type ion-doped buried layer is above and in connection to the first type ion-doped well;

forming a shallow trench isolation structure in the first type ion-doped well; removing a portion of the first type ion-doped well to form an opening that exposes the first type ion-doped buried layer;

forming a dielectric layer over the substrate;

forming at least one first contact opening and at least one second contact opening in the dielectric layer, wherein the first contact opening exposes a portion of the

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metal silicide layer and the second contact opening exposes the first type ion-doped well at the bottom of the shallow trench isolation structure;

forming a second type ion-doped region in the first type ion-doped region at the bottom of the shallow trench isolation structure; and

- forming a contact inside the first contact opening and the second contact opening.
- 23. The method of claim 22, wherein the step of forming the second type ion-doped region includes:
- conducting an ion implant operation to form the second type ion-doped region in the first type ion-doped well at the bottom of the second contact opening.
- 24. The method of claim 22, wherein the second type ion-doped region is formed in the same step as forming the shallow trench isolation structure, and the step of forming the second type ion-doped region and the shallow trench isolation structure includes the substeps of:
- forming a shallow trench isolation opening in the first type ion-doped well; conducting an ion implant operation to form the second type ion-doped region in the first type ion-doped well at the bottom of the shallow trench isolation opening; and forming the shallow trench isolation structure inside the shallow trench isolation opening.
- 25. The method of claim 24, wherein the variable capacitor further includes a liner layer within the shallow trench isolation opening.

- 26. The method of claim 22, wherein between the step of forming the opening and the step of forming the dielectric layer, further includes forming a metal silicide layer on the first type ion-doped buried layer.
- 27. The method of claim 26, wherein between the step of forming the opening and themetal silicide layer, further includes forming a spacer on each sidewall of the opening.